

## SOT-89-3L Plastic-Encapsulate Transistors

TRANSISTOR (NPN)

### FEATURES

- Epitaxial planar die construction
- Complementary PNP Type available(PXT2907A)

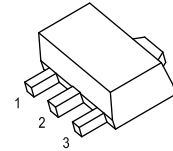
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MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	75	V
$V_{CEO}$	Collector-Emitter Voltage	40	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current -Continuous	800	mA
$P_C$	Collector Power Dissipation	0.5	W
$T_J$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55 ~ 150	$^{\circ}\text{C}$

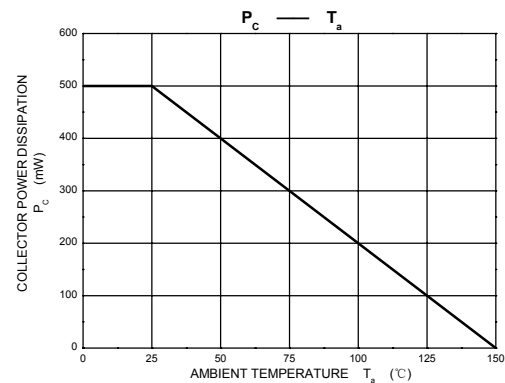
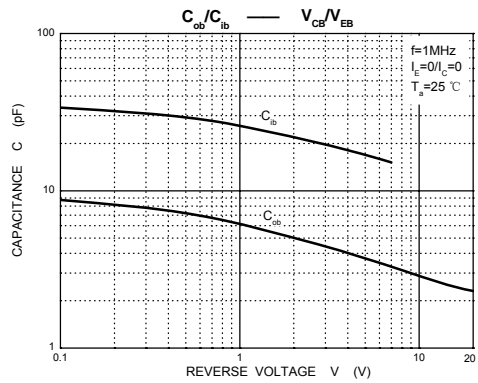
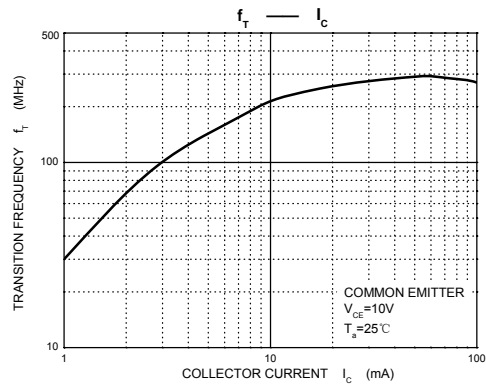
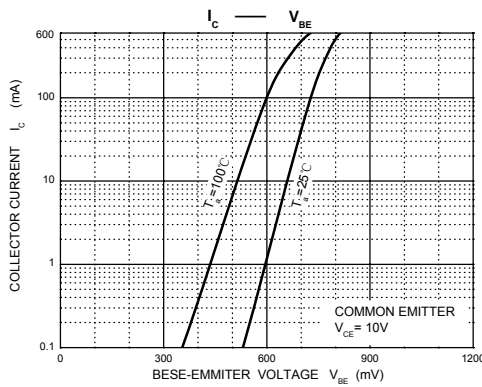
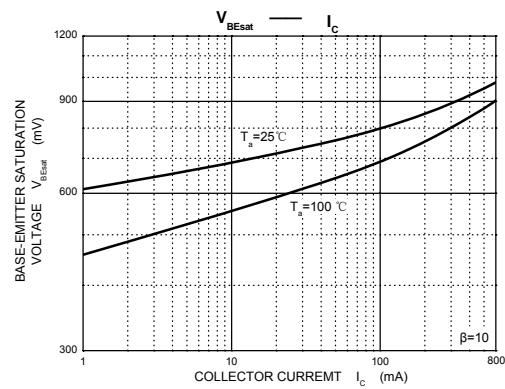
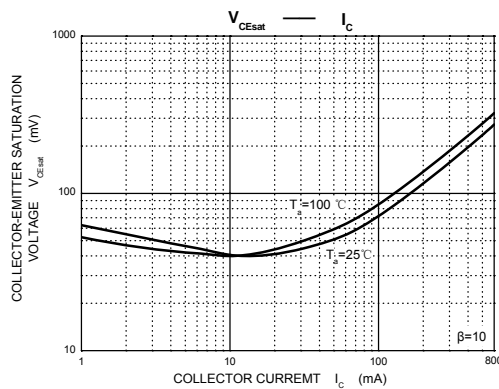
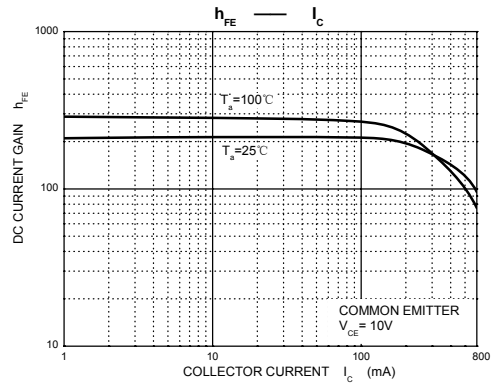
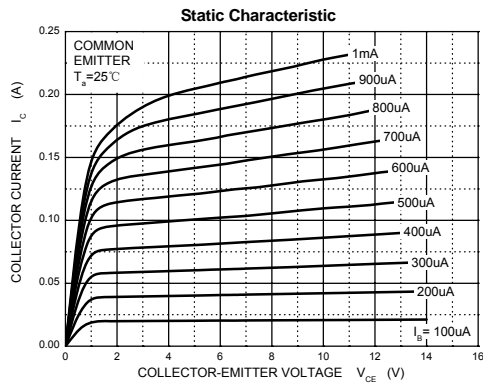
### SOT-89-3L

1. BASE
2. COLLECTOR
3. EMITTER

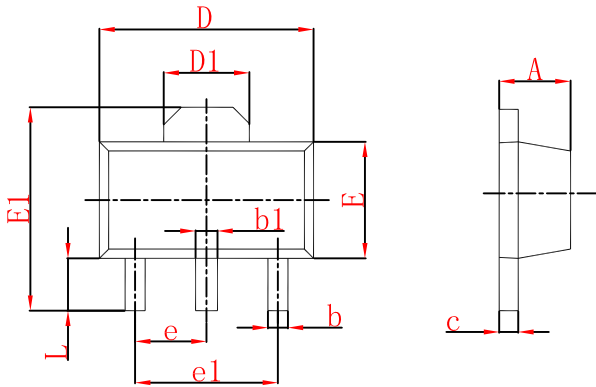


ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$  unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}, I_E = 0$	75		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}, I_B = 0$	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}, I_C = 0$	6		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = 60\text{V}, I_E = 0$		0.01	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 5\text{V}, I_C = 0$		0.01	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE} = 10\text{V}, I_C = 0.1\text{mA}$	35		
	$h_{FE(2)}$	$V_{CE} = 10\text{V}, I_C = 1\text{mA}$	50		
	$h_{FE(3)}$	$V_{CE} = 10\text{V}, I_C = 10\text{mA}$	75		
	$h_{FE(4)}$	$V_{CE} = 10\text{V}, I_C = 150\text{mA}$	100	300	
	$h_{FE(5)}$	$V_{CE} = 1\text{V}, I_C = 150\text{mA}$	50		
	$h_{FE(6)}$	$V_{CE} = 10\text{V}, I_C = 500\text{mA}$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$		1	V
	$V_{CE(sat)}$	$I_C = 150\text{mA}, I_B = 15\text{mA}$		0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$		2.0	V
	$V_{BE(sat)}$	$I_C = 150\text{mA}, I_B = 15\text{mA}$	0.6	1.2	V
Transition frequency	$f_T$	$V_{CE} = 10\text{V}, I_C = 20\text{mA}$ $f = 100\text{MHz}$	300		MHz
Output Capacitance	$C_{ob}$	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		8	pF
Delay time	$t_d$	$V_{CC} = 30\text{V}, I_C = 150\text{mA}$		10	ns
Rise time	$t_r$	$V_{BE(off)} = 0.5\text{V}, I_{B1} = 15\text{mA}$		25	ns
Storage time	$t_s$	$V_{CC} = 30\text{V}, I_C = 150\text{mA}$		225	ns
Fall time	$t_f$	$I_{B1} = -I_{B2} = 15\text{mA}$		60	ns

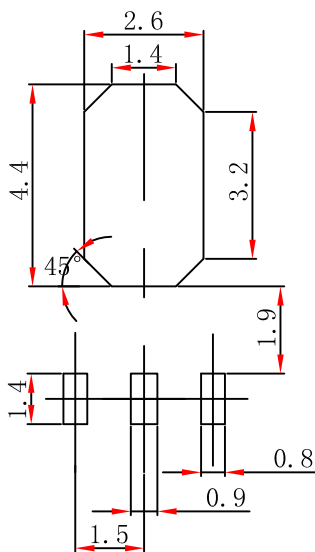


## SOT-89-3L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

## SOT-89-3L Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05$ mm.
3. The pad layout is for reference purposes only.

单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)